

Actualize a spectrum closest to the sunlight

#### Mid-Power LED – 3030 Series

S1S0-3030xx9506-00000000-00001 (Cool, Neutral, Warm)

















## **Product Brief**

#### **Description**

- This White Colored surface-mount LED comes in standard package dimension. Package Size: 3.0x3.0x0.6mm
- It has a substrate made up of a molded plastic reflector sitting on top of a lead frame.
- The die is attached within the reflector cavity and the cavity is encapsulated by silicone.
- The package design coupled with careful selection of component materials allow these products to perform with high reliability.

#### **Features and Benefits**

- Thermally Enhanced Package Design
- Mid Power to High Power up to 1W
- Max. Driving Current 200mA
- Compact Package Size
- High Color Quality with CRI Min.95 (R9>85)
- Pb-free Reflow Soldering Application
- Eye Safety (Exempt 5000K)

#### **Key Applications**

- Replacement lamps Bulb, Tube
- Commercial
- Industrial
- Residential

**Table 1. Product Selection Table** 

5.	0.1	Nominal	5 . 11 . 1	CRI	
Reference Code (	Color	ССТ	Part Number	Min	
		6500K	S1S0-3030659506-00000000-00001		
STW9C2SB-S	Cool White	5700K S1S0-3030579506-00000000-00001			
		5000K	5000K S1S0-3030509506-00000000-00001		
	Neutral White	4000K	S1S0-3030409506-00000000-00001	– 95	
	Warm - White	3500K	S1S0-3030359506-00000000-00001	_	
		3000K	S1S0-3030309506-00000000-00001	_	
		2700K	S1S0-3030279506-00000000-00001	_	

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## **Performance Characteristics**

Table 2. Product Selection Guide,  $I_F = 150 \text{mA}$ ,  $T_j = 25^{\circ}\text{C}$ , RH30%

Min. CRI, R <sub>a</sub> <sup>(4)</sup>	Nominal CCT [K] <sup>[1]</sup>	Min. Flux [lm]	Typ. Luminous Flux Φ <sub>V</sub> <sup>[3]</sup> [lm] @150mA	Typ. Luminous Efficacy [lm/W] @150mA	Part Number
	6500	90.7	95	101	\$1\$0-3030659506 -00000000-00001
	5700	90.7	96	101	\$1\$0-3030579506 -00000000-00001
	5000	90.7	101	107	\$1\$0-3030509506 -00000000-00001
95	4000	90.2	100	106	S1S0-3030409506 -00000000-00001
	3500	83.2	99	105	\$1\$0-3030359506 -00000000-00001
	3000	83.2	93	97	S1S0-3030309506 -00000000-00001
	2700	83.2	89	93	S1S0-3030279506 -00000000-00001

#### Notes:

- (1) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.
- (2) Seoul Semiconductor maintains a tolerance of  $\pm 5\%$  on Intensity and power measurements. The luminous intensity IV was measured at the peak of the spatial pattern which may not be aligned with the mechanical axis of the LED package.
- (3) The lumen table is only for reference.

## **Performance Characteristics**

Table 3. Characteristics, I<sub>F</sub>=150mA, T<sub>i</sub>= 25°C, RH30%

Parameter	Symbol	Value			Unit
r al allietei	Symbol	Min.	Тур.	Max.	
Forward Current	I <sub>F</sub>	-	150	-	mA
Forward Voltage <sup>[1]</sup>	$V_{F}$	6.2	-	6.6	V
Luminous Intensity (5000K) <sup>[1]</sup>	I <sub>v</sub>	-	30 (103.7)	-	cd (lm)
CRI <sup>[1]</sup>	R <sub>a</sub>	95	-	-	
Viewing Angle [2]	2O <sub>1/2</sub>	-	120	-	Deg.
Thermal resistance (J to S) [3]	Rθ <sub>J-S</sub>	-	10	-	°C/W
ESD Sensitivity(HBM)	-	- Class 3A JESD22-A114-E			

**Table 4. Absolute Maximum Ratings** 

Parameter	Symbol	Value	Unit
Forward Current	I <sub>F</sub>	200	mA
Power Dissipation	$P_{D}$	1.32	W
Junction Temperature	T <sub>j</sub>	125	°C
Operating Temperature	T <sub>opr</sub>	-40~ + 85	°C
Storage Temperature	$T_{stg}$	-40 ~ + 100	°C

#### Notes:

(1) Tolerance : VF : $\pm$ 0.1V, IV : $\pm$ 5%, Ra : $\pm$ 2, x,y : $\pm$ 0.005

(2)  $2\Theta_{1/2}$  is the off-axis where the luminous intensity is 1/2 of the peak intensity.

(3) Thermal resistance : Rth<sub>JS</sub> (Junction / solder)

- (4) It is recommended to use it in the condition that the reliability is secured within the Max value.
- LED's properties might be different from suggested values like above and below tables if
  operation condition will be exceeded our parameter range. Care is to be taken that power
  dissipation does not exceed the absolute maximum rating of the product.
- Thermal resistance can be increased substantially depending on the heat sink design/operating condition, and the maximum possible driving current will decrease accordingly.
- All measurements were made under the standardized environment of Seoul Semiconductor.

Fig 1. Color Spectrum, T<sub>i</sub>= 25°C

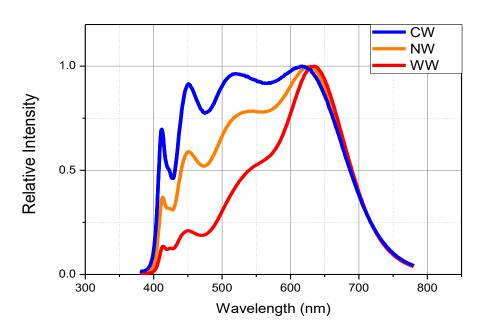
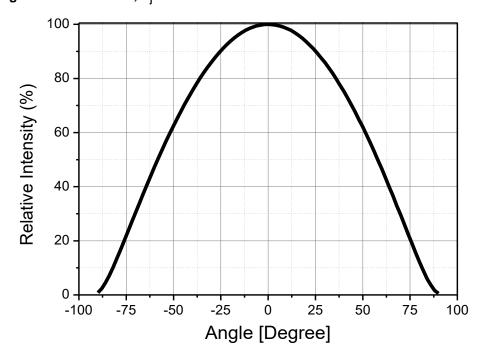


Fig 2. Radiant Pattern, T<sub>i</sub>= 25°C



# **Characteristics Graph**

Fig 3. Forward Voltage vs. Forward Current,  $T_j = 25^{\circ}C$ 

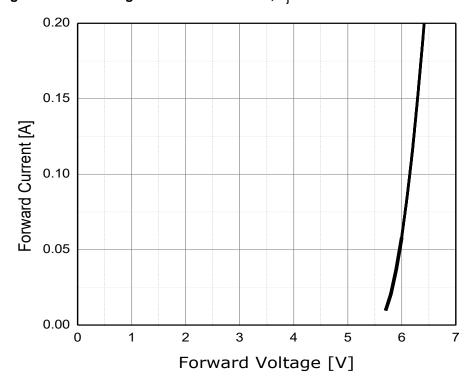
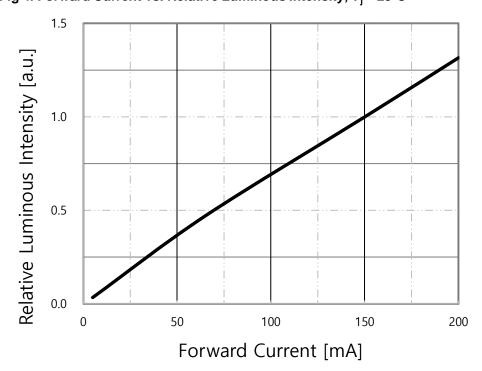
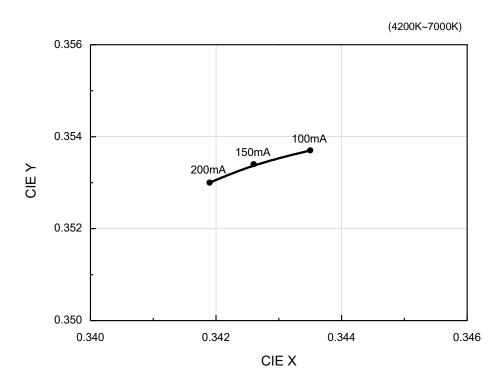
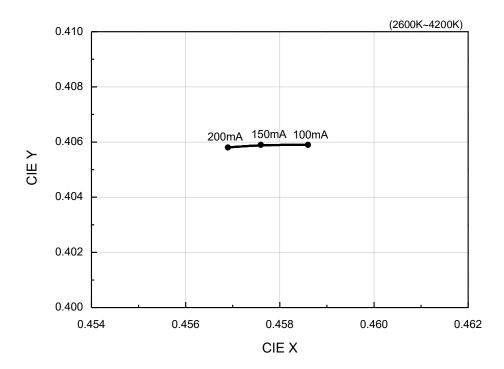


Fig 4. Forward Current vs. Relative Luminous Intensity, T<sub>i</sub> = 25°C



## Fig 5. Forward Current vs. CIE X, Y Shift, $T_j = 25^{\circ}C$





## Fig 6. Junction Temperature vs. Relative Luminous Intensity, I<sub>F</sub>=150mA

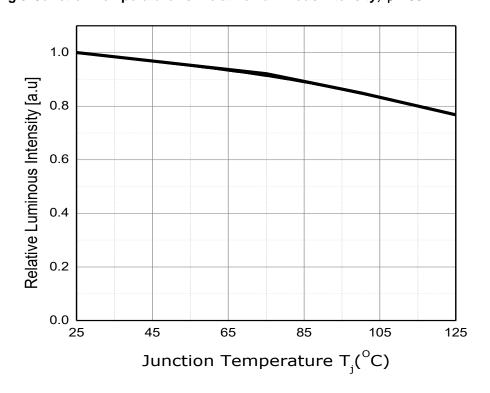
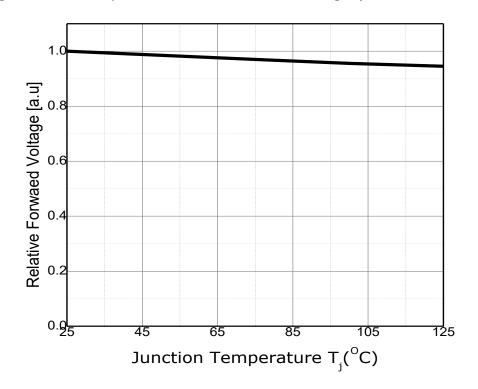
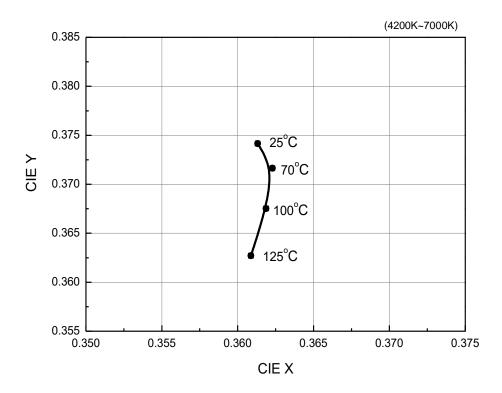
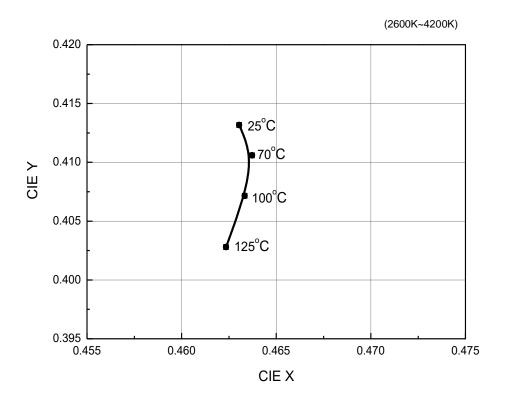


Fig 7. Junction Temperature vs. Relative Forward Voltage, I<sub>F</sub>=150mA



#### Fig 8. Chromaticity Coordinate vs. Junction Temperature, I<sub>F</sub>=150mA





# **Characteristics Graph**

Fig 9. Ambient Temperature vs. Maximum Forward Current,  $T_{j\_max}$  = 125°C

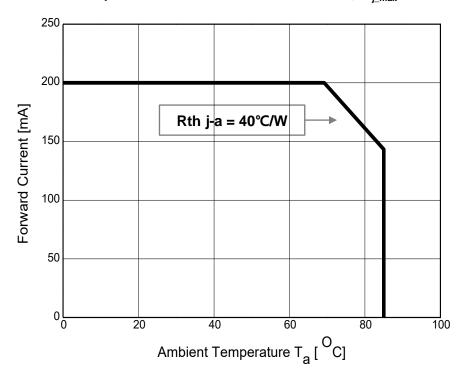


Table 5. Bin Code description,  $T_j=25$ °C,  $I_F=150$ mA

Part Number	Luminous Flux (lm) @5000K			Color Chromaticity	Typical Forward Voltage (V)		
	Bin Code	Min.	Max.	Coordinate	Bin Code	Min.	Max.
S1S0-	K28	90.7	97.2	•	Z62	6.2	6.4
3030xx9506-	L30	97.2	103.7	_	Z64	6.4	6.6
00000000-00001	L32	103.7	110.2	-			

#### Table 6. Intensity rank distribution

Available ranks

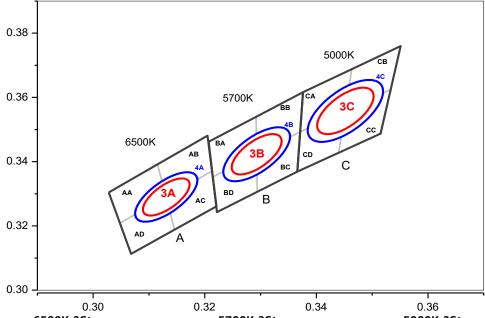
сст	CIE	IV Rank				
6000 ~ 7000K	Α	K26	K28	L30	L32	
5300 ~ 6000K	В	K26	K28	L30	L32	
4700 ~ 5300K	С	K26	K28	L30	L32	
3700 ~ 4200K	E	K26	K28	L30	L32	
2900 ~ 3200K	G	K26	K28	L30	L32	
2600 ~ 2900K	Н	K26	K28	L30	L32	

#### \*Notes:

All measurements were made under the standardized environment of Seoul Semiconductor. In order to ensure availability, single color rank will not be orderable.

## **Color Bin Structure**

## CIE Chromaticity Diagram (Cool white), T<sub>j</sub>=25°C, I<sub>F</sub>=150mA



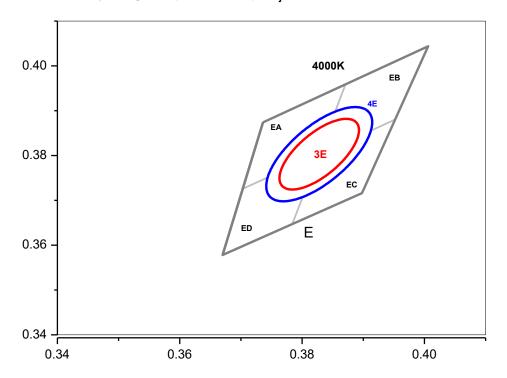
6500	K 3Step	5700	K 3Step	5000K 3Step		
3A			3B	3C		
Center point	0.3123 : 0.3282	Center point	0.3287 : 0.3417	Center point	0.3447 : 0.3553	
Major Axis a	0.0066	Major Axis a	0.0071	Major Axis a	0.0081	
Minor Axis b	0.0027	Minor Axis b	0.0030	Minor Axis b	0.0035	
Ellipse	58	Ellipse Rotation Angle		Ellipse	60	
<b>Rotation Angle</b>	50			Rotation Angle	00	

6500	K 4Step	<u>5700</u>	K 4Step	5000K 4Step		
4A			4B	4C		
Center point	0.3123 : 0.3282	Center point	0.3287 : 0.3417	Center point	0.3447 : 0.3553	
Major Axis a	0.0088	Major Axis a	0.0095	Major Axis a	0.0108	
Minor Axis b	0.0036	Minor Axis b	0.0040	Minor Axis b	0.0047	
Ellipse	<b>5</b> 0	Ellipse		Ellipse	60	
Rotation Angle	tation Angle 58		Rotation Angle 59			

Α	A	А	В	Α	С	Α	D
CIE X	CIE Y						
0.3028	0.3304	0.3115	0.3393	0.3131	0.329	0.3048	0.3209
0.3048	0.3209	0.3131	0.329	0.3146	0.3187	0.3068	0.3113
0.3131	0.329	0.3213	0.3371	0.3221	0.3261	0.3146	0.3187
0.3115	0.3393	0.3205	0.3481	0.3213	0.3371	0.3131	0.329
В	A	В	В	В	C	В	D
CIE X	CIE Y						
0.3207	0.3462	0.3292	0.3539	0.3293	0.3423	0.3215	0.3353
0.3215	0.3353	0.3293	0.3423	0.3294	0.3306	0.3222	0.3243
0.3293	0.3423	0.3371	0.3493	0.3366	0.3369	0.3294	0.3306
0.3292	0.3539	0.3376	0.3616	0.3371	0.3493	0.3293	0.3423
С	A	c	В	C	C	C	D
CIE X	CIE Y						
0.3376	0.3616	0.3463	0.3687	0.3452	0.3558	0.3371	0.3493
0.3371	0.3493	0.3452	0.3558	0.344	0.3428	0.3366	0.3369
0.3452	0.3558	0.3533	0.3624	0.3514	0.3487	0.344	0.3428
0.3463	0.3687	0.3551	0.376	0.3533	0.3624	0.3452	0.3558

## **Color Bin Structure**

## CIE Chromaticity Diagram (Cool white), T<sub>j</sub>=25°C, I<sub>F</sub>=150mA



4000K 3Step						
;	3E					
Center point	0.3818 : 0.3797					
Major Axis a	0.0094					
Minor Axis b	0.0040					
Ellipse Rotation Angle	53					

 4000K 4Step

 4E

 Center point
 0.3818:0.3797

 Major Axis a
 0.0125

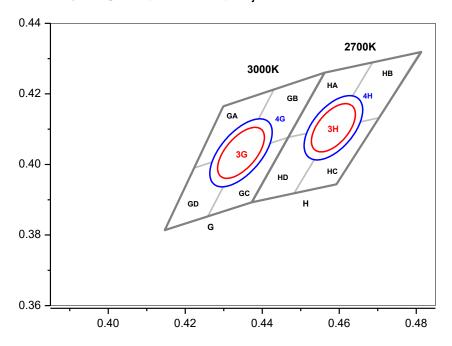
 Minor Axis b
 0.0053

 Ellipse Rotation Angle
 53

Α	E	В	E	c	E	D
CIE Y	CIE X	CIE Y	CIE X	CIE Y	CIE X	CIE Y
0.3874	0.3871	0.3959	0.3828	0.3803	0.3703	0.3726
0.3726	0.3828	0.3803	0.3784	0.3647	0.367	0.3578
0.3803	0.3952	0.388	0.3898	0.3716	0.3784	0.3647
0.3959	0.4006	0.4044	0.3952	0.388	0.3828	0.3803
	CIE Y 0.3874 0.3726 0.3803	CIE Y CIE X  0.3874 0.3871  0.3726 0.3828  0.3803 0.3952	CIE Y         CIE X         CIE Y           0.3874         0.3871         0.3959           0.3726         0.3828         0.3803           0.3803         0.3952         0.388	CIE Y         CIE X         CIE Y         CIE X           0.3874         0.3871         0.3959         0.3828           0.3726         0.3828         0.3803         0.3784           0.3803         0.3952         0.388         0.3898	CIE Y         CIE X         CIE Y         CIE X         CIE Y           0.3874         0.3871         0.3959         0.3828         0.3803           0.3726         0.3828         0.3803         0.3784         0.3647           0.3803         0.3952         0.388         0.3898         0.3716	CIE Y         CIE X         CIE Y         CIE X         CIE Y         CIE X           0.3874         0.3871         0.3959         0.3828         0.3803         0.3703           0.3726         0.3828         0.3803         0.3784         0.3647         0.367           0.3803         0.3952         0.388         0.3898         0.3716         0.3784

## **Color Bin Structure**

## CIE Chromaticity Diagram (Cool white), $T_j=25$ °C, $I_F=150$ mA



3000K 3Step		2700K 3Step		
3 Step		3 Step		
Center point	0.4338 : 0.4030	Center point	0.4578 : 0.4101	
Major Axis a	0.0085	Major Axis a	0.0079	
Minor Axis b	0.0041	Minor Axis b	0.0041	
Ellipse	53	Ellipse	54	
Rotation Angle	55	Rotation Angle	54	

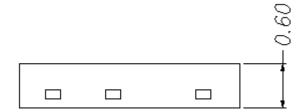
3000K 4Step		2700K 4Step		
4 Step		4 Step		
Center point	0.4338 : 0.4030	Center point	0.4578 : 0.4101	
Major Axis a	0.0113	Major Axis a	0.0105	
Minor Axis b	0.0055	Minor Axis b	0.0055	
Ellipse	53	Ellipse	54	
Rotation Angle		Rotation Angle		

G	A	G	В	G	С	G	D
CIE X	CIE Y	CIE X	CIE Y	CIE X	CIE Y	CIE X	CIE Y
0.4299	0.4165	0.443	0.4212	0.4345	0.4033	0.4223	0.399
0.4223	0.399	0.4345	0.4033	0.4259	0.3853	0.4147	0.3814
0.4345	0.4033	0.4468	0.4077	0.4373	0.3893	0.4259	0.3853
0.443	0.4212	0.4562	0.426	0.4468	0.4077	0.4345	0.4033
Н	A	н	В	н	c	H	D
CIE X	CIE Y	CIE X	CIE Y	CIE X	CIE Y	CIE X	CIE Y
				0.= /\		0.2 / (	U.= .
0.4562	0.426	0.4687	0.4289	0.4585	0.4104	0.4468	0.4077
0.4562 0.4468	0.426 0.4077	0.4687 0.4585	0.4289 0.4104				
				0.4585	0.4104	0.4468	0.4077

# Top View Bottom View 3.00 Cathode 1.53 0.47 0.50

## **Side View**

Anode (+)

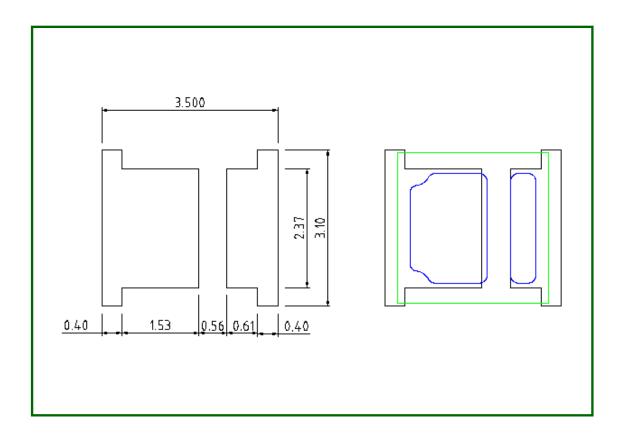


(1) All dimensions are in millimeters.

(2) Scale: none

(3) Undefined tolerance is  $\pm 0.2$ mm

## **Recommended Solder Pad**



#### Notes:

- (1) All dimensions are in millimeters.
- (2) Scale: none
- (3) This drawing without tolerances are for reference only
- (4) Undefined tolerance is  $\pm 0.1 \text{mm}$

# **Reflow Soldering Characteristics**

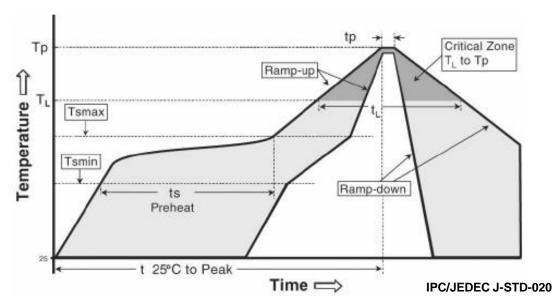


Table 7.

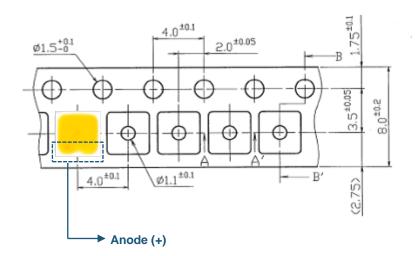
Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (Tsmax to Tp)	3° C/second max.	3° C/second max.
Preheat		
- Temperature Min (Tsmin)	100 °C	150 °C
- Temperature Max (Tsmax)	150 °C	200 °C
- Time (Tsmin to Tsmax) (ts)	60-120 seconds	60-180 seconds
Time maintained above:		
- Temperature (TL)	183 °C	217 °C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature (Tp)	215℃	260℃
Time within 5°C of actual Peak Temperature (tp)2	10-30 seconds	20-40 seconds
Ramp-down Rate	6 °C/second max.	6 °C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

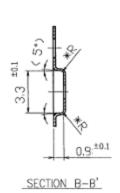
#### Caution

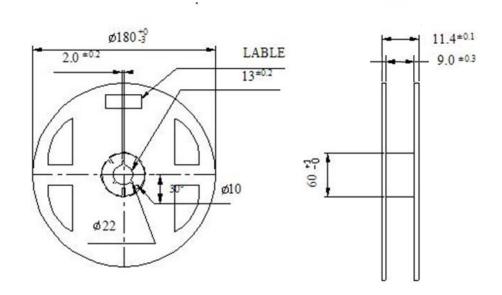
- (1) Reflow soldering is recommended not to be done more than two times. In the case of more than 24 hours passed soldering after first, LEDs will be damaged.
- (2) Repairs should not be done after the LEDs have been soldered. When repair is unavoidable, suitable tools must be used.
- (3) Die slug is to be soldered.
- (4) When soldering, do not put stress on the LEDs during heating.
- (5) After soldering, do not warp the circuit board.



## **Emitter Tape & Reel Packing**







( Tolerance:  $\pm 0.2$ , Unit: mm )

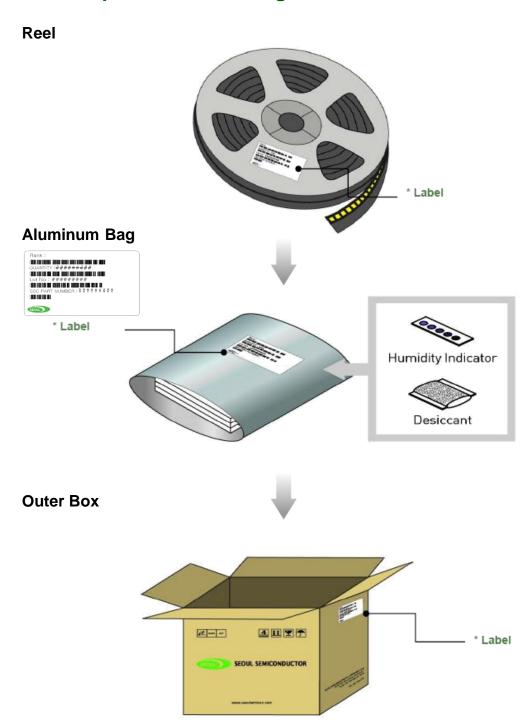
- (1) Quantity: 4,500pcs/Reel
- (2) Cumulative Tolerance : Cumulative Tolerance/10 pitches to be  $\pm 0.2$ mm
- (3) Adhesion Strength to be 0.1-0.7N when

Adhesion strength to be 0.1-0.7N when the cover tape is turned off from the carrier tape at the angle of 10° to the carrier tape.

(4) Package: P/N, Manufacturing data Code No. and Quantity to be indicated on a damp proof Package.



# **Emitter Tape & Reel Packing**



**Product Nomenclature** 

#### **\$1\$0-3030xx9506-00000000-00001** – Mid-Power LED

## Table 8. Part Numbering System : X<sub>1</sub>X<sub>2</sub>X<sub>3</sub>X<sub>4</sub>X<sub>5</sub>X<sub>6</sub>X<sub>7</sub>X<sub>8</sub>-X<sub>9</sub>X<sub>10</sub>

Part Number Code	Description	Part Number	Value
<b>X</b> <sub>1</sub>	Company	S	Seoul Semiconductor
X <sub>2</sub>	Level of Integration	1	Discrete LED
X <sub>3</sub> X <sub>4</sub>	Technology	S0	Sunlike
X <sub>5</sub> X <sub>6</sub> X <sub>7</sub> X <sub>8</sub>	Dimension	3030	
X <sub>9</sub> X <sub>10</sub>	CCT	xx	
X <sub>11</sub> X <sub>12</sub>	CRI	95	
X <sub>13</sub> X <sub>14</sub>	Vf	06	
X <sub>15</sub> X <sub>16</sub> X <sub>17</sub>	Characteristic code Flux Rank		
X <sub>18</sub> X <sub>19</sub> X <sub>20</sub>	Characteristic code Vf Rank 000		
X <sub>21</sub> X <sub>22</sub>	X <sub>21</sub> X <sub>22</sub> Characteristic code Color Step		
X <sub>23</sub> X <sub>24</sub>	Туре	00	
X <sub>25</sub> X <sub>26</sub> X <sub>27</sub>	Internal code	Internal code 001	

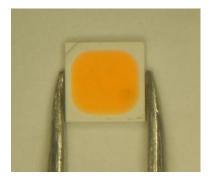


## **Handling of Silicone Resin for LEDs**

(1) During processing, mechanical stress on the surface should be minimized as much as possible. Sharp objects of all types should not be used to pierce the sealing compound.



(2) In general, LEDs should only be handled from the side. By the way, this also applies to LEDs without a silicone sealant, since the surface can also become scratched.



- (3) When populating boards in SMT production, there are basically no restrictions regarding the form of the pick and place nozzle, except that mechanical pressure on the surface of the resin must be prevented. This is assured by choosing a pick and place nozzle which is larger than the LED's reflector area.
- (4) Silicone differs from materials conventionally used for the manufacturing of LEDs. These conditions must be considered during the handling of such devices. Compared to standard encapsulants, silicone is generally softer, and the surface is more likely to attract dust.

As mentioned previously, the increased sensitivity to dust requires special care during processing. In cases where a minimal level of dirt and dust particles cannot be guaranteed, a suitable cleaning solution must be applied to the surface after the soldering of components.

- (5) SSC suggests using isopropyl alcohol for cleaning. In case other solvents are used, it must be assured that these solvents do not dissolve the package or resin.

  Ultrasonic cleaning is not recommended. Ultrasonic cleaning may cause damage to the LED.
- (6) Please do not mold this product into another resin (epoxy, urethane, etc) and do not handle this. product with acid or sulfur material in sealed space.



#### (1) Storage

To avoid the moisture penetration, we recommend store in a dry box with a desiccant. The recommended storage temperature range is 5°C to 30°C and a maximum humidity of RH50%.

(2) Use Precaution after Opening the Packaging Use SMT techniques properly when you solder the LED as separation of the lens may affect the light output efficiency.

#### Pay attention to the following:

- a. Recommend conditions after opening the package
  - -Sealing / Temperature : 5 ~ 40°CHumidity : less than RH30%
- b. If the package has been opened more than 4 week(MSL\_2a) or the color of the desiccant changes, components should be dried for 10-12hr at 60±5°C
- (3) Do not apply mechanical force or excess vibration during the cooling process to normal temperature after soldering.
- (4) Do not rapidly cool device after soldering.
- (5) Components should not be mounted on warped (non coplanar) portion of PCB.
- (6) Radioactive exposure is not considered for the products listed here in.
- (7) Gallium arsenide is used in some of the products listed in this publication. These products are dangerous if they are burned or shredded in the process of disposal. It is also dangerous to drink the liquid or inhale the gas generated by such products when chemically disposed of.
- (8) This device should not be used in any type of fluid such as water, oil, organic solvent and etc. When washing is required, IPA (Isopropyl Alcohol) should be used.
- (9) When the LEDs are in operation the maximum current should be decided after measuring the package temperature.

- (10) The appearance and specifications of the product may be modified for improvement without notice.
- (11) Long time exposure of sunlight or occasional UV exposure will cause lens discoloration.
- (12) VOCs (Volatile organic compounds) emitted from materials used in the construction of fixtures can penetrate silicone encapsulants of LEDs and discolor when exposed to heat and photonic energy. The result can be a significant loss of light output from the fixture. Knowledge of the properties of the materials selected to be used in the construction of fixtures can help prevent these issues.
- (13) Attaching LEDs, do not use adhesives that outgas organic vapor.
- (14) The driving circuit must be designed to allow forward voltage only when it is ON or OFF.
  If the reverse voltage is applied to LED, migration can be generated resulting in LED damage.
- (15) Similar to most Solid state devices;
  LEDs are sensitive to Electro-Static Discharge (ESD) and Electrical Over Stress (EOS).
  Below is a list of suggestions that Seoul Semiconductor purposes to minimize these effects.
- a. ESD (Electro Static Discharge)

Electrostatic discharge (ESD) is the defined as the release of static electricity when two objects come into contact. While most ESD events are considered harmless, it can be an expensive problem in many industrial environments during production and storage. The damage from ESD to an LEDs may cause the product to demonstrate unusual characteristics such as:

- Increase in reverse leakage current lowered turn-on voltage
- Abnormal emissions from the LED at low current

The following recommendations are suggested to help minimize the potential for an ESD event. One or more recommended work area suggestions:

- Ionizing fan setup
- ESD table/shelf mat made of conductive materials
- ESD safe storage containers

One or more personnel suggestion options:

- Antistatic wrist-strap
- Antistatic material shoes
- Antistatic clothes

#### Environmental controls:

- Humidity control (ESD gets worse in a dry environment)



#### b. EOS (Electrical Over Stress)

Electrical Over-Stress (EOS) is defined as damage that may occur when an electronic device is subjected to a current or voltage that is beyond the maximum specification limits of the device. The effects from an EOS event can be noticed through product performance like:

- Changes to the performance of the LED package
  (If the damage is around the bond pad area and since the package is completely encapsulated the package may turn on but flicker show severe performance degradation.)
- Changes to the light output of the luminaire from component failure
- Components on the board not operating at determined drive power

Failure of performance from entire fixture due to changes in circuit voltage and current across total circuit causing trickle down failures. It is impossible to predict the failure mode of every LED exposed to electrical overstress as the failure modes have been investigated to vary, but there are some common signs that will indicate an EOS event has occurred:

- Damaged may be noticed to the bond wires (appearing similar to a blown fuse)
- Damage to the bond pads located on the emission surface of the LED package (shadowing can be noticed around the bond pads while viewing through a microscope)
- Anomalies noticed in the encapsulation and phosphor around the bond wires.
- This damage usually appears due to the thermal stress produced during the EOS event.
- c. To help minimize the damage from an EOS event Seoul Semiconductor recommends utilizing:
  - A surge protection circuit
  - An appropriately rated over voltage protection device
  - A current limiting device



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#### **Company Information**

Seoul Semiconductor (www.SeoulSemicon.com) manufacturers and packages a wide selection of light emitting diodes (LEDs) for the automotive, general illumination/lighting, Home appliance, signage and back lighting markets. The company is the world's fifth largest LED supplier, holding more than 10,000 patents globally, while offering a wide range of LED technology and production capacity in areas such as "nPola", "Acrich", the world's first commercially produced AC LED, and "Acrich MJT - Multi-Junction Technology" a proprietary family of high-voltage LEDs.

The company's broad product portfolio includes a wide array of package and device choices such as Acrich and Acirch2, high-brightness LEDs, mid-power LEDs, side-view LEDs, and through-hole type LEDs as well as custom modules, displays, and sensors.

#### **Legal Disclaimer**

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# **Revision History**

Revision	Date	Page	Remarks
3.0	20.05.28	ALL	이전 담당자 작성
3.1	20.09.14	4p 26p	노트 (4) 추가 Revision history 추가

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